

L Number	Hits	Search Text	DB	Time stamp
-	994	((438/131) or (438/467) or (438/600) or (438/771) or (438/474) or (438/798)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/18 07:50
-	370	((438/131) or (438/467) or (438/600) or (438/771) or (438/474) or (438/798)).CCLS.) and plasma	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/01 08:34
-	172	((438/131) or (438/467) or (438/600) or (438/771) or (438/474) or (438/798)).CCLS.) and (plasma with oxid\$5)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/01 08:37
-	49	((438/131) or (438/467) or (438/600) or (438/771) or (438/474) or (438/798)).CCLS.) and (plasma with oxid\$5)) and (antifuse)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/01 08:40
-	240	(oxidizing near plasma) and semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/01 08:49
-	5	(oxidizing near plasma) same (Ge or germanium)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/01 08:41
-	2	("6420215").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/01 09:03
-	4	("3913224").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/01 08:52
-	1	"20020136045"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/01 08:52
-	0	6420215.URPN.	USPAT	2003/04/01 09:02
-	18	("3913224"   "4272880"   "4442507"   "4489478"   "4498226"   "4499557"   "4543594"   "4876220"   "4881114"   "5070384"   "5306935"   "5427979"   "5535156"   "5745407"   "5831325"   "5835396"   "5838530"   "6034882").PN.	USPAT	2003/04/01 09:02
-	251	(method near oxidation) with plasma	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/01 09:04
-	0	((method near oxidation) with plasma) and antifuse	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/01 09:05
-	23	(plasma adj oxidation) and antifuse	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/01 09:13

-	1	"20030026157"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/01 09:15
-	765	(365/225.7).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/01 09:15
-	3	((365/225.7).CCLS.) and (plasma adj oxidation)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/01 09:16
-	1877	365/51	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/01 09:16
-	8	365/51 and (plasma adj oxidation)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/01 09:17
-	1128	438/778	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/14 10:29
-	993	438/778	USPAT; EPO; JPO; DERWENT; IBM_TDB	2003/04/14 10:30
-	552	438/778 and plasma	USPAT; EPO; JPO; DERWENT; IBM_TDB	2003/04/14 10:33
-	539	((oxidat\$4 with (conduct\$3)) same plasma	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/18 07:53
-	338	((oxidat\$4 with (conduct\$3)) same plasma) and semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/18 07:51
-	214	((oxidat\$4 with (conduct\$3)) same plasma) and semiconductor	USPAT	2003/04/18 07:52
-	318	((oxidat\$4 with (conducting or conductive)) same plasma)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/18 07:54
-	0	((oxidat\$4 with (conducting or conductive)) same plasma) and semicondcutor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/18 07:54
-	194	((oxidat\$4 with (conducting or conductive)) same plasma) and semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/18 07:54
-	122	((oxidat\$4 with (conducting or conductive)) same plasma) and semiconductor	USPAT	2003/04/18 08:00
-	2	("6461982").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/18 08:00

-	1054	plasma and (reaction near kinetics)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/20 15:56
-	64	plasma and ( oxid\$4 same (reaction near kinetics))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/20 15:57
-	24	plasma and ( oxid\$4 same (reaction near kinetics)) and semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/20 16:02
-	320	plasma and ( oxid\$4 same (exposure near time)) and semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/20 16:09
-	154	plasma and ( oxid\$4 same (exposure near time)) and semiconductor and (silicon near oxide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/20 16:21
-	1	("6583006").PN.	USPAT	2003/11/20 16:22